

Miniaturized Microstrip Suppressing Cell with Wide Stopband

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Abstract — In this paper, based on simple stepped impedance structures a methodology is followed to design a very compact size lowpass filter (LPF) as a suppressing cell. The proposed suppressing cell consists of stepped impedance ladder-type resonators, which provides a wide stopband by creating the transmission zeros to its frequency response. The proposed suppressing cell has clear advantages like low insertion loss in the passband and suitable roll-off. The designed LPF is fabricated on a microstrip layout and tested. The measured results highlight the efficiency of the filter and have a good agreement with the simulated results. With mentioned expression, the fabricated LPF can be a powerful block as a suppressing cell to implement in the distributed high frequency circuits.

Index Terms — Lowpass filter, microstrip, miniaturized, stepped impedance structure, suppressing cell.

I. INTRODUCTION

Design of the high frequency circuits are highly extended and demanded, in the modern technologies. Handset devices and wireless communications depend on the high frequency circuits and the suppression of the spurious signals is an important requirement in this field [1]. The position of the lowpass filters is undeniable in order to block and suppress the unwanted harmonics. From the introducing of microstrip technology until now, many microstrip structures and many methods have been presented to design the high efficient LPFs [1-14]. Planar structures are widely used for their simple fabrication and design in [1-13], which have sharp transition band and wide stopband, but these LPFs suffers from the big size, which makes them inappropriate as the suppressing cells to use in hybrid high frequency circuits, in addition to their almost low

attenuation levels in their stopbands.

A miniaturized LPF with very sharp roll-off has been designed to eliminate the unwanted harmonics for a Wilkinson power divider in [14], which has a so narrow stopband bandwidth. In [15], using defected ground structures (DGS), an Elliptic-function LPF has been fabricated with sharp roll-off, this technique design not only is not easy to implement but also has disadvantages such as large circuit size and narrow stopband width. A lowpass filter has been designed in [16] with sharp roll-off as a miniaturized LPF, but it is not so compact and has a very narrow rejection bandwidth. In [17], the fabricated LPF has a compact structure, although the stopband region is not wide enough. A wide stopband LPF has been presented in [18], but this filter suffers from its high insertion loss in the passband and its large circuit size. In [19-24], the low value of maximum variation of the group delay in the passband has been introduced as an effective factor in LPF designs, which it tried to be improved in the proposed work. Also, the simple geometry and topology of the designed filter is a significant specification, which can be effective in fabrication and implementation. Therefore the design of a simple structure and high efficient LPF is the main objective of this paper.

In this paper, using stepped impedance microstrip stubs and ladder-type structures, a miniaturized LPF with good rejection bandwidth is designed. The LPF has -3 dB cut-off frequency at 4 GHz. The rejection band is achieved from 5 to 23.3 GHz. A simple methodology is used to design this filter that follows in the next session. All the simulations are done using Agilent Advanced Design System (ADS) software, and all of the microstrip layouts are designed and fabricated on RT/Duriod5880 substrate with dielectric constant (ϵ_r) of 2.22, the thickness of 0.508 mm and the loss tangent of 0.0009.

II. SUPPRESSING CELL DESIGN

At the first step, Elliptic function resonator layout has been selected and expanded using high and low impedance lines, as shown in Fig. 1. The physical lengths of the low-impedance and high-impedance lines are calculated using below equations [10]:

$$L_i = \frac{g_i Z_0}{2\pi f_c g_0}, \quad (1)$$

$$C_i = \frac{g_i g_0}{2\pi f_c Z_0}, \quad (2)$$

$$d_{L_i} = \frac{\lambda_{g_{L_i}}}{2\pi} \sin^{-1}\left(\frac{2\pi f_c L_i}{Z_{0L}}\right), \quad (3)$$

$$d_{C_i} = \frac{\lambda_{g_{C_i}}}{2\pi} \sin^{-1}(2\pi f_c C_i Z_{0C}), \quad (4)$$

where, Z_{0C_i} and Z_{0L_i} are corresponded to the impedance transmission lines with low and high impedance, respectively. g_i and g_0 are the element values of each part of the prototype layout, $\lambda_{g_{L_i}}$ and $\lambda_{g_{C_i}}$ are the guided wavelengths of high and low impedance lines, respectively. With considering the Fig. 1, the ABCD matrix for the proposed resonator can be written as:

$$\begin{bmatrix} A & B \\ C & D \end{bmatrix} = \begin{bmatrix} 1 & \frac{Z_{oc3}}{2} \\ 0 & 1 \end{bmatrix} \times \begin{bmatrix} 1 & 0 \\ Y_{oc1} + Y_{oc2} + Y_{oL1} + Y_{oL2} & 1 \end{bmatrix} \times \begin{bmatrix} 1 & \frac{Z_{oc3}}{2} \\ 0 & 1 \end{bmatrix}, \quad (5)$$

where, Y_{oc1} , Y_{oc2} , Y_{oL1} and Y_{oL2} are the admittances of the high and low impedance transmission lines, which are indicted in Fig. 1. With calculation, the Equation (5) can be simplified in:

$$\begin{bmatrix} A & B \\ C & D \end{bmatrix} = \begin{bmatrix} 1 & Z_{oc3} \\ 0 & 1 \end{bmatrix} \times \begin{bmatrix} 1 & 0 \\ Y_T & 1 \end{bmatrix} = \begin{bmatrix} 1 + Z_{oc3} Y_T & Z_{oc3} \\ Y_T & 1 \end{bmatrix}, \quad (6)$$

where, $Y_T = Y_{oc1} + Y_{oc2} + Y_{oL1} + Y_{oL2}$.

The proposed resonator has a symmetric shape as illustrated in Fig. 1; so clearly, it is expected that the resonator must have a reciprocal response. Therefore, the determinant of the ABCD matrix must be equal to 1. The determinant of the ABCD matrix can be calculated from Equation 6 as:

$$\Delta \begin{bmatrix} A & B \\ C & D \end{bmatrix} = 1 + Z_{oc3} Y_T - Z_{oc3} Y_T = 1. \quad (7)$$

Then, the Equation (7) validates the achieved ABCD matrix of the proposed resonator. The simulated S-parameters of the proposed resonator are shown in Fig. 2. As considered, in the passband the resonator has a transmission pole at 2.87 GHz with attenuation level of -15.6 dB and in the stopband the resonator has a transmission zero at 8.5 GHz with attenuation level of -64.3 dB with -3 dB cut-off frequency at 5.6 GHz. The resonator has a smooth passband region; although it has a narrow rejection bandwidth and gradual response in the transition band.

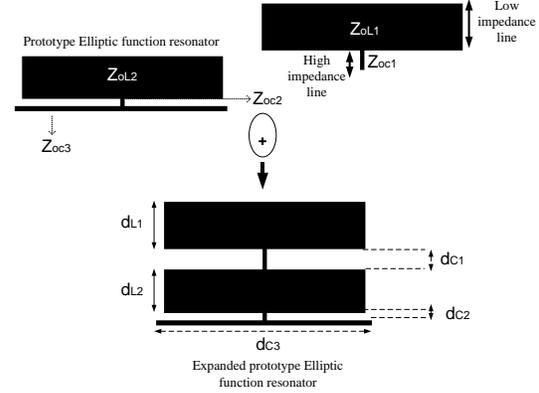


Fig. 1. The layout implementation procedure for the proposed expanded prototype Elliptic function resonator.

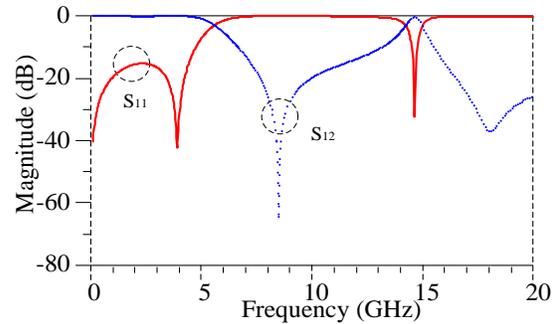


Fig. 2. Simulated S-parameters of the proposed expanded prototype Elliptic function resonator.

For this structure, the LC model for the proposed resonator is extracted as shown in Fig. 3. In this model, C represents the overall capacitance of low impedance stubs (Z_{oL1} , Z_{oL2}) respect to ground; L1 represents the overall inductance of high impedance lines (Z_{oC1} , Z_{oC2}); L represents the inductance of high impedance line of Z_{oC3} .

A comparison of the S21 parameters of this model and layout is shown in Fig. 4. The values of the lumped elements are illustrated in this figure, which are the conventional values of an Elliptic function 3 order resonator with -3 dB cut off frequency at 5.6 GHz. Transfer function for the calculation of the first transmission zero has been extracted using the proposed LC model as below:

$$T(s) = \frac{(9.793 \times 10^9)s^2 + 2.789 \times 10^{31}}{s^3 + (3.398 \times 10^{10})s^2 + (1.539 \times 10^{21})s + 2.789 \times 10^{31}}. \quad (8)$$

In this equation, the coefficients of the polynomials of the numerator and denominator depends on the capacitances and inductances values of the LC model

and the location of transmission zero can be adjusted by changing these values. For example, as seen in Fig. 5, by increasing the lengths of d_{L1} and d_{L2} from 1 mm to 1.5 mm, due to increment of the capacitance of C, which is the total capacitance of Z_{OL1} and Z_{OL2} , first transmission zero moves from 8.4 GHz to 7.2 GHz. Also, by decreasing the lengths of d_{L1} and d_{L2} from 1mm to 0.5 mm, due to decrement of the capacitance of C, first transmission zero moves to 11.4 GHz.

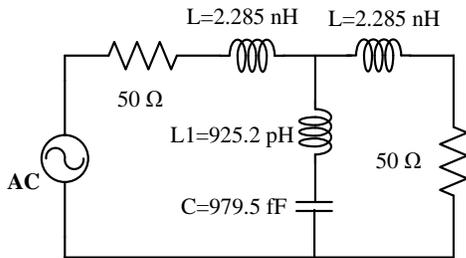


Fig. 3. The LC model for the proposed resonator.

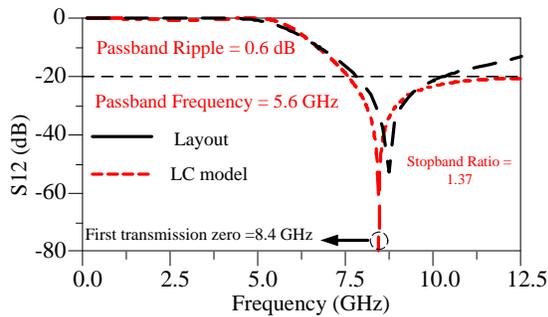


Fig. 4. A comparison of the S21 parameters of LC model and layout of the proposed resonator.

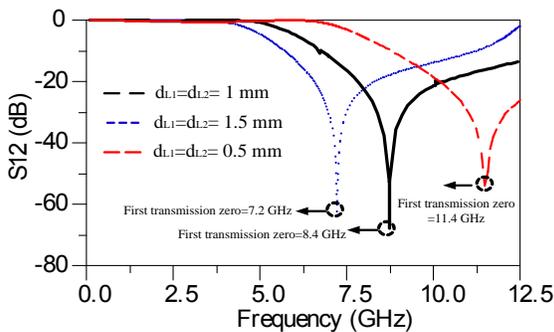


Fig. 5. Simulated S21 parameter of the proposed resonator as a function of d_{L1} and d_{L2} .

To modify the frequency response, another resonator can be cascaded to the previous one with the same dimensions as shown in Fig. 6. These dimensions are as follows: $W = 1$ mm, $W1 = 1.1$ mm, $d = 4.8$ mm, $d2 = 0.5$ mm

and $d3 = 11$ mm. Using Equation (7), the ABCD matrix for the proposed cascaded resonator can be written as:

$$\begin{bmatrix} A & B \\ C & D \end{bmatrix} = \begin{bmatrix} 1 + Z_{oc3}Y_T & Z_{oc3} \\ Y_T & 1 \end{bmatrix} \times \begin{bmatrix} 1 + Z_{oc3}Y_T & Z_{oc3} \\ Y_T & 1 \end{bmatrix} \quad (9)$$

The simulated S12-parameter of the proposed cascaded resonator is shown in Fig. 7. As seen, by moving the existence transmission zero to the lower frequency at 6.8 GHz and creating a new transmission zero at 10.7 GHz; the -3 dB cut-off frequency moves to 5 GHz with sharper transition band. Also, wider rejection band can be obtained. It has a stopband bandwidth from 5.9 GHz to 13 GHz for the attenuation level of -20 dB. But, the rejection band is so narrow yet. To extend the stopband width enough, the proposed cascaded resonator can be improved by adding another resonator, symmetrically with same dimensions as the proposed filter, as shown in Fig. 8. Thus, the stopband bandwidth has been improved up to 157% of the previous rejection band. Also, two stubs are added to the feeding lines at input and output to match the proposed filter to 50 Ω coaxial line. The ABCD matrix for the proposed cascaded symmetric resonator can be written using symmetric rules for impedances and with considering Equation 9 as:

$$\begin{bmatrix} A & B \\ C & D \end{bmatrix} = \begin{bmatrix} 1 + 2Z_{oc3}Y_{Ts} & 2Z_{oc3} \\ Y_{Ts} & 1 \end{bmatrix} \begin{bmatrix} 1 + 2Z_{oc3}Y_{Ts} & 2Z_{oc3} \\ Y_{Ts} & 1 \end{bmatrix} \quad (10)$$

where, $Y_{Ts} = 1/2 (Y_{oc1} + Y_{oc2}) + 2(Y_{oL1} + Y_{oL2})$.

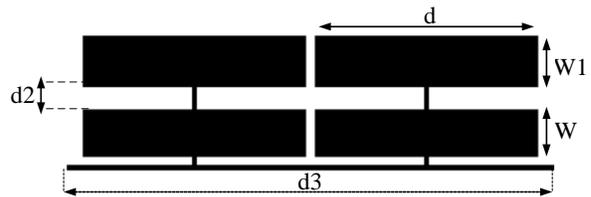


Fig. 6. The proposed cascaded resonator.

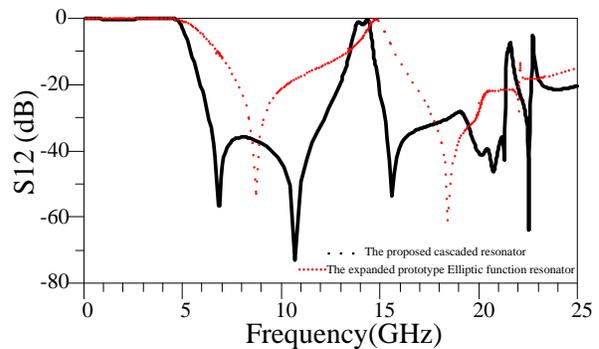


Fig. 7. The simulated S12-parameter of the proposed cascaded resonator.

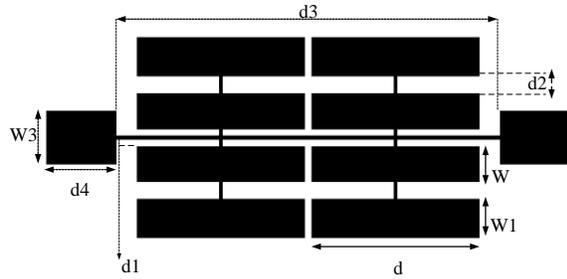


Fig. 8. The layout of the proposed LPF.

III. RESULTS

The designed LPF has been fabricated on RT/Duriod5880 substrate with dielectric constant (ϵ_r) of 2.22, the thickness of 0.508 mm and the loss tangent of 0.0009 and is illustrated in Fig. 9. The mentioned dimensions in the Fig. 8 are determined using equations (1-10) and tuned using ADS as a tuning tool. These dimensions are as follows: $W = 1$ mm, $W1 = 1.1$ mm, $W2 = 0.1$ mm, $W3 = 1.5$ mm, $d = 4.8$ mm, $d1 = 0.2$ mm, $d2 = 0.5$ mm, $d3 = 11$ mm and $d4 = 2$ mm. The measurements are done using HP8757A network analyzer. The simulated and measured S-parameters of the fabricated LPF are shown in Fig. 10. As seen, the -3 dB cut-off frequency is placed at 4 GHz. The rejection band is extended from 5 to 23.3 GHz with corresponding attenuation level of 16.6 dB. Also, the return loss is about 0 dB in the more space of the rejection band. The maximum insertion loss in the 90% of the passband region is 0.1 dB, where the maximum return loss is 15.6 dB. The physical size of the fabricated circuit, which occupies very small area, is only $11 \text{ mm} \times 5.5 \text{ mm} = 60.5 \text{ mm}^2$ ($0.197\lambda_g \times 0.098\lambda_g$), where λ_g is the guided wave length at -3 dB cut-off frequency. A comparison between the characteristics of the proposed LPF and some referred works are shown in Table 1. In this table, RL (dB) and IL (dB) are the maximum return loss and insertion loss in the passband region, respectively.

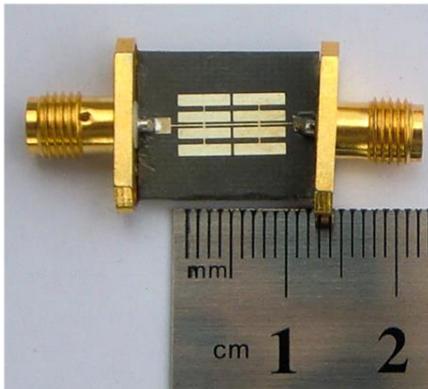


Fig. 9. Photograph of the fabricated LPF.

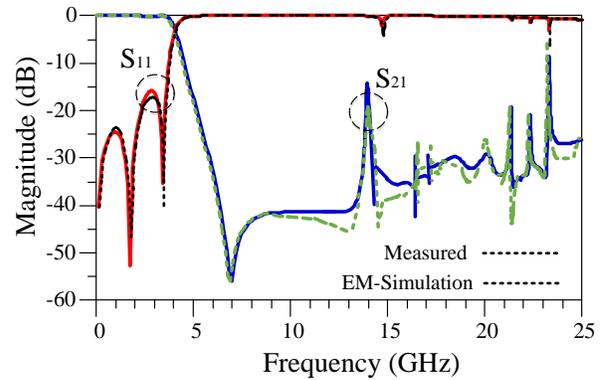


Fig. 10. The simulated and measured S-parameters of the fabricated LPF.

As can be seen in Table 1, the proposed LPF has the smallest size (60.3 mm) and the best insertion loss (0.1) among the referred filters. The good specifications of the rejection band and the small size are the important factors, which show that the proposed filter can be used in compact modern high frequency circuits as a suppressing cell in order to suppress the unwanted harmonics and interferences. The group delay of a microwave filter has a relationship to the insertion loss of a filter and design of a filter with flat group delay in the passband region is desirable [18-24]. As seen in Fig. 11, maximum variation of the measured group delay in the passband has not a significant variation and has a dispensable value and is only 0.23 ns. Table 2 shows a comparison between the maximum variation of the measured group delay in the passband for the proposed LPF and some referred works with reported group delay. As illustrated, the proposed filter has the best performance in the case of group delay.

Table 1: Performance comparisons between the proposed LPF and some referred works

Ref.	f_c (GHz)	SF	SBW/ f_c	Size (mm^2)	RL (dB)	IL (dB)
2	5.45	2	5.7	221	15	0.12
3	2	1	8.4	482	10	1.00
4	1.78	2	2.8	643.7	~10	0.30
5	1.67	1	5.9	100	12	0.50
6	1	2	4.1	638.4	20	0.40
12	1.18	1.5	5.9	174.2	-	-
13	1.5	2	12.1	364	20	0.13
14	3.6	2	1.9	59.8	~15	0.11
15	2.4	2	2.2	284	17	0.30
16	1.5	1.5	0.9	269	10	-
17	4.16	2	3	83.7	11	0.11
18	2.3	2	9.5	169.1	~10	1.80
This work	4	1.6	4.6	60.5	~15	0.10

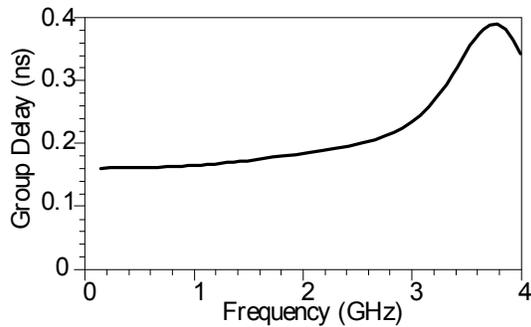


Fig. 11. The measured group delay in the passband for the proposed LPF.

Table 2: A comparison between the maximum variations of the measured group delay between some referred works with reported group delay

Ref	f_c (GHz)	Maximum Variation of the Group Delay in the Passband (ns)	Resonator Structure
19	1.1	0.5	Tapered
20	1.74	0.5	Butterfly-shaped
21	1.55	0.5	Semi-circle stepped impedance
22	3.55	0.4	Spiral
23	2.37	0.44	Stub loaded semi-circle stepped-impedance
24	4	0.27	T-Shaped, patch and stepped impedance
This work	4	0.23	Stepped impedance

IV. CONCLUSION

A miniaturized LPF has been proposed with wide rejection band as a small size and efficient suppressing cell. The proposed LPF rejects the spurious signals from 5 GHz to 23.3 GHz with attenuation level of 16.6 dB. The maximum variation of the measured group delay in the passband region is only 0.23 ns, which is the less value in comparison with some reported works. The measurement results clear the accuracy of the simulations.

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